ABSTRACT

METHOD FOR RECYCLING AN EPITAXIED DONOR WAFER

The invention relates to a method of forming a structure comprising a thin layer (5, 50) made of a semiconductor material on a receiver wafer (B), including the following steps:

- surface preparation (13) by removal of a thickness (Tr) of material from a layer (4) formed by epitaxial growth on a support substrate (1);
- transfer of part (5, 50) of the epitaxied layer to the receiver wafer (B) so as to form the thin layer on the receiver wafer, a negative (A') also being formed that includes the support substrate (1) and a remaining non-transferred part (40) of the epitaxied layer,

characterised in that the thickness (Tr) removed by the said surface preparation step is adapted such that application of the said surface preparation step to the negative (A') enables the formation of a new thin layer from the remaining part (40) which thickness has been reduced by the surface preparation step.

Figure 1